

APPLIED PHYSICS DEPARTMENT

DST-FIST and UGC-DRS aided department
The Maharaja Sayajirao University of Baroda, Vadodara



**Appointment for the post of Junior Research Fellow [JRF] and
Research Associate [RA] for DAE/BRNS Project**

**TITLE OF RESEARCH PROJECT:
'RELIABILITY AND LIFETIME IMPROVEMENT OF HIGH POWER LASER DIODES:
PROTECTION AGAINST FAILURE MODES'**

Applications are invited for one post of Junior Research Fellow and one post of Research Associate in DAE/BRNS research project for a period of three years to work in the area of Semiconductor Laser Diodes.

For JRF

1. *Essential Qualification:* Fresh First class M.Sc. Degree in Physics/Applied Physics (Specialization in Laser Physics/Optoelectronics/Electronics).
2. *Stipend:* Rs 10,000 p.m. (for three years) with House Rent Allowance (HRA) and Medical Allowance (MA) benefits.

For RA

1. *Essential Qualification:* Ph.D. Degree in Physics/Applied Physics (Specialization in Laser Physics/Optoelectronics/Electronics).
2. *Stipend:* Rs 16,000 p.m. (for three years) with House Rent Allowance (HRA) and Medical Allowance (MA) benefits.

Type-written application with complete Bio-data with E-mail ID should reach (*by speed-post/courier only*) to

Dr Chetan Panchal

Principal Investigator, DAE/BRNS Project (Laser Diode)
Applied Physics Department
Faculty of Technology and Engineering
The M.S. University of Baroda
Vadodara 390 001, India
E-mail: cjpanchal_msu@yahoo.com
Mobile: +91 9825094761

before **25 June 2008**.

Affix a recent passport size photograph on the right top corner of the first page of application. Please mention the post applied for (JRF or RA) on application cover.

The interview of eligible candidates will be conducted on 30 June 2008 at Dean's office (Room No. 2), Faculty of Technology and Engineering from 11 a.m. onwards. Please bring your original documents at the time of interview.

NOTE: No TA/DA will be given for attending the interview.